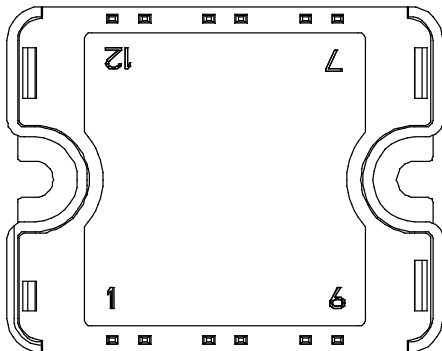
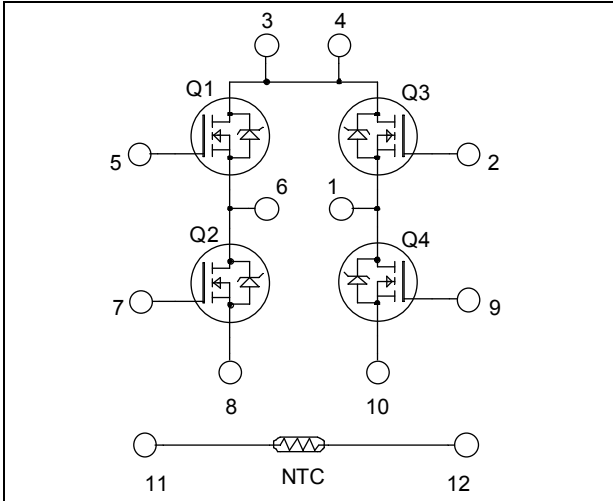


Full - Bridge MOSFET Power Module

$V_{DSS} = 600V$
 $R_{DSon} = 190m\Omega$ typ @ $T_j = 25^\circ C$
 $I_D = 20A$ @ $T_c = 25^\circ C$



Pins 3/4 must be shorted together

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Power MOS 8™ FREDFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Fast intrinsic reverse diode
 - Avalanche energy rated
 - Very rugged
- Very low stray inductance
 - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	600	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	20
		$T_c = 80^\circ C$	15
I_{DM}	Pulsed Drain current	125	
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	230	m Ω
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	208
I_{AR}	Avalanche current (repetitive and non repetitive)	17	A

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 600\text{V}$ $V_{GS} = 0\text{V}$	$T_j = 25^\circ\text{C}$		250	μA
			$T_j = 125^\circ\text{C}$		1000	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10\text{V}, I_D = 17\text{A}$		190	230	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 1\text{mA}$	3	4	5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30\text{V}$			± 100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$ $V_{DS} = 25\text{V}$ $f = 1\text{MHz}$		5316		pF
C_{oss}	Output Capacitance			610		
C_{rss}	Reverse Transfer Capacitance			56		
Q_g	Total gate Charge	$V_{GS} = 10\text{V}$ $V_{Bus} = 300\text{V}$ $I_D = 17\text{A}$		165		nC
Q_{gs}	Gate – Source Charge			36		
Q_{gd}	Gate – Drain Charge			70		
$T_{d(on)}$	Turn-on Delay Time	Resistive switching @ 25°C $V_{GS} = 15\text{V}$ $V_{Bus} = 400\text{V}$ $I_D = 17\text{A}$ $R_G = 4.7\Omega$		37		ns
T_r	Rise Time			43		
$T_{d(off)}$	Turn-off Delay Time			115		
T_f	Fall Time			34		

Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_S	Continuous Source current (Body diode)		$T_c = 25^\circ\text{C}$		20	A
			$T_c = 80^\circ\text{C}$		15	
V_{SD}	Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = -17\text{A}$			1	V
dv/dt	Peak Diode Recovery ❶				30	V/ns
t_{rr}	Reverse Recovery Time	$I_S = -17\text{A}$ $V_R = 100\text{V}$ $di_S/dt = 100\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		200	ns
			$T_j = 125^\circ\text{C}$		370	
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$	0.76		μC
			$T_j = 125^\circ\text{C}$	1.91		

❶ dv/dt numbers reflect the limitations of the circuit rather than the device itself.

$$I_S \leq -17\text{A} \quad di/dt \leq 1000\text{A}/\mu\text{s} \quad V_{DD} \leq 400\text{V} \quad T_j \leq 125^\circ\text{C}$$

Thermal and package characteristics

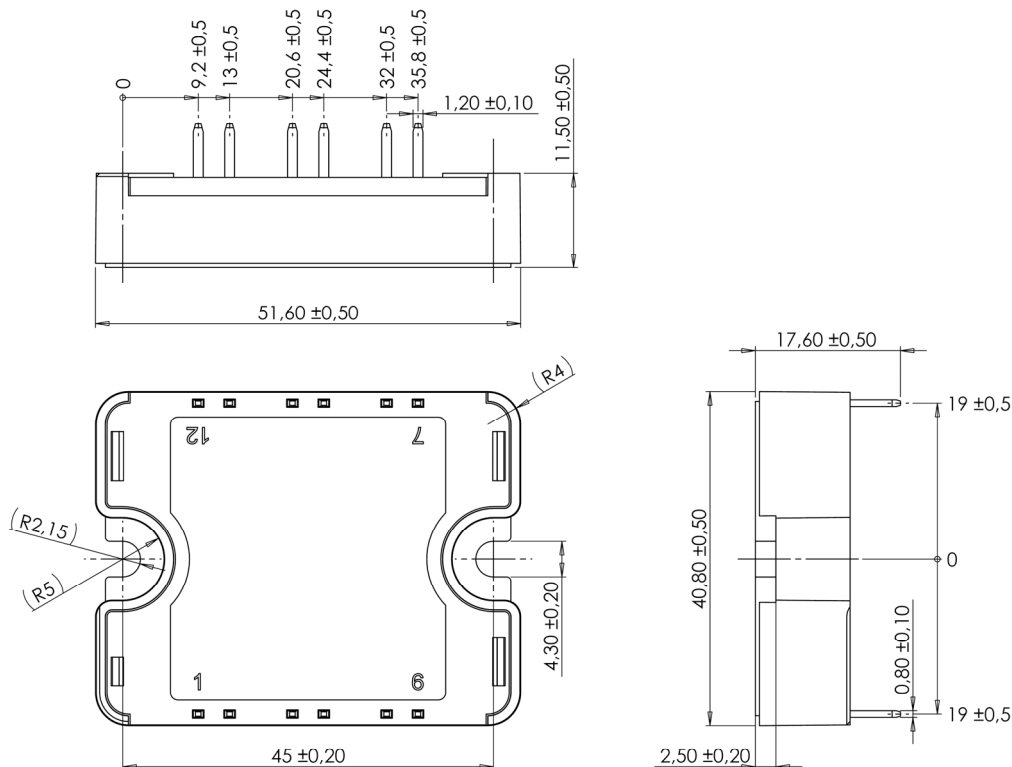
Symbol	Characteristic	Min	Typ	Max	Unit	
R _{thJC}	Junction to Case Thermal Resistance			0.6	°C/W	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, 50/60Hz	4000			V	
T _J	Operating junction temperature range	-40		150	°C	
T _{STG}	Storage Temperature Range	-40		125		
T _C	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight			80		g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
ΔR ₂₅ /R ₂₅			5		%
B _{25/85}	T ₂₅ = 298.15 K		3952		K
ΔB/B	T _C = 100°C		4		%

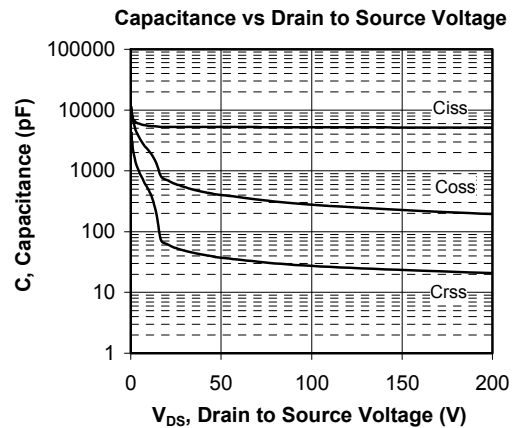
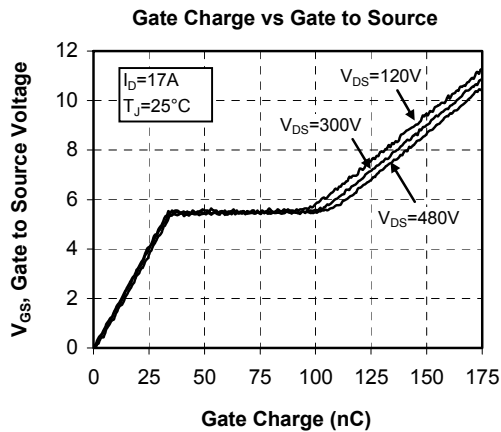
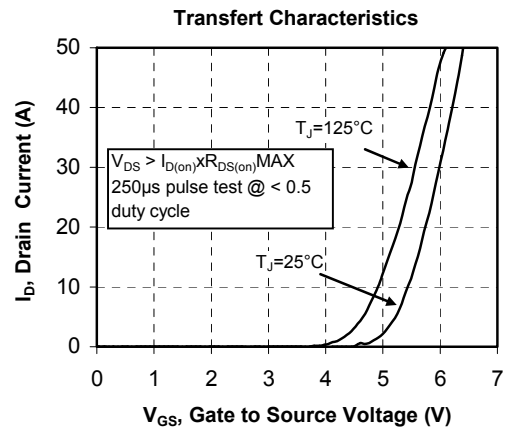
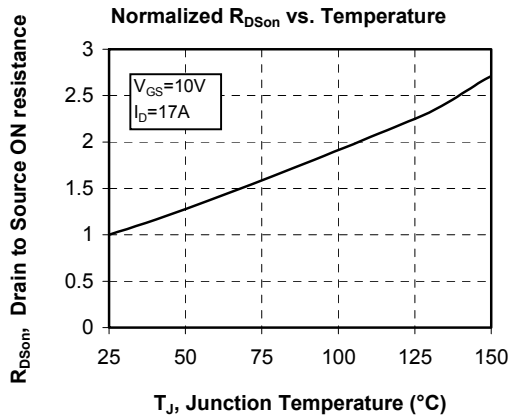
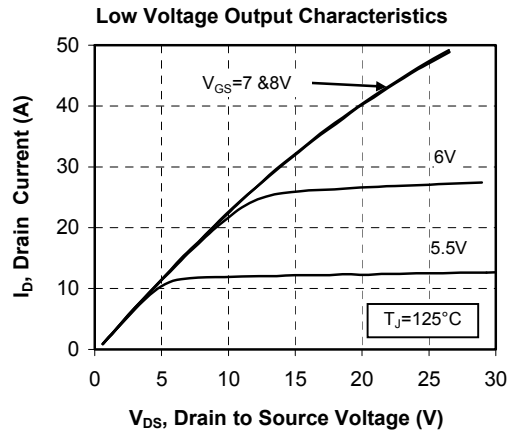
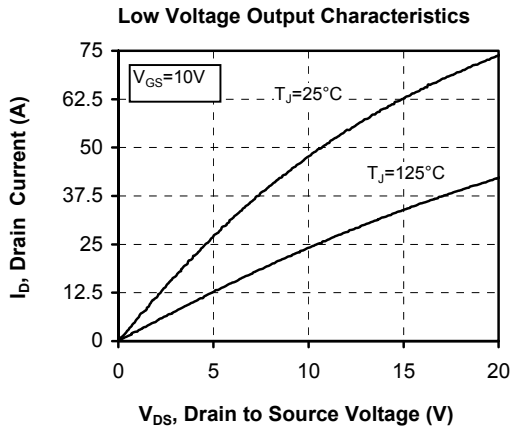
$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
 R_T: Thermistor value at T

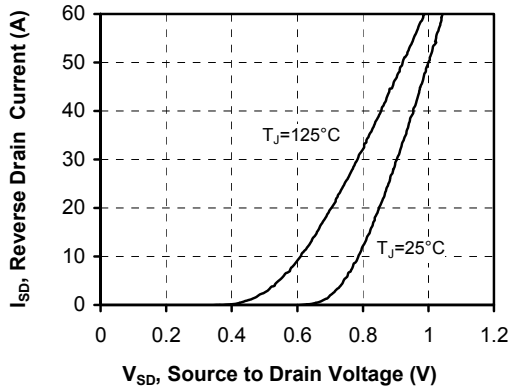
SP1 Package outline (dimensions in mm)


See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

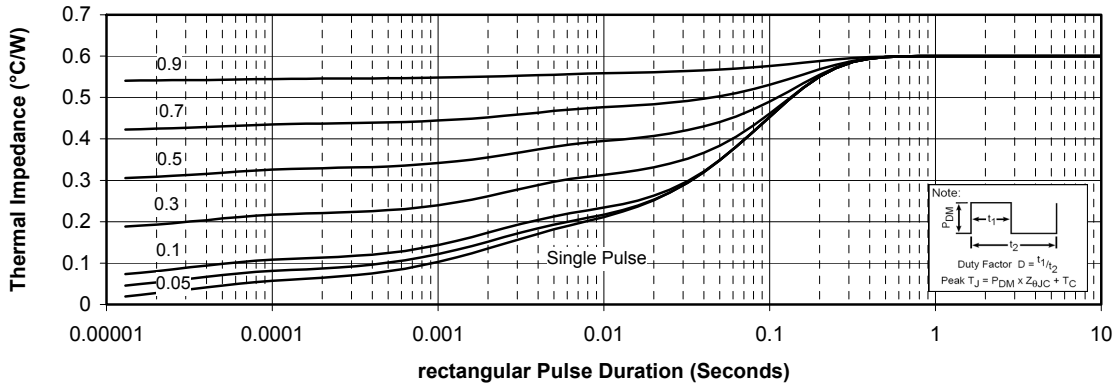
Typical Performance Curve



Drain Current vs Source to Drain Voltage



Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration



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